

## Descriptions

This -20V 2.8A P-Channel MOSFET in a SOT-23 Plastic Package.

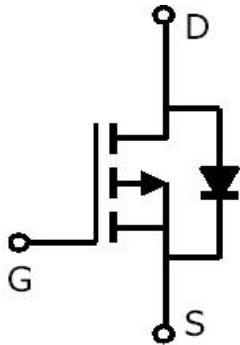
## Features

- Super high dense cell design for low  $R_{DS(ON)}$
- SOT-23 package
- Halogen-Free product

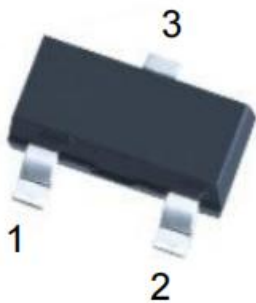
## Applications

Primarily the display screen drive applications.

## Equivalent Circuit



## Pinning



PIN1: Gate

PIN 2: Source

PIN 3: Drain

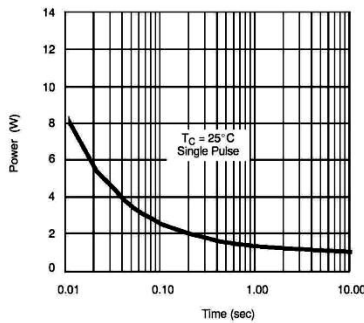
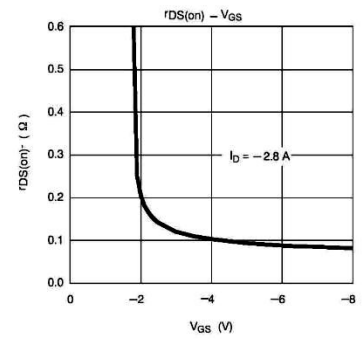
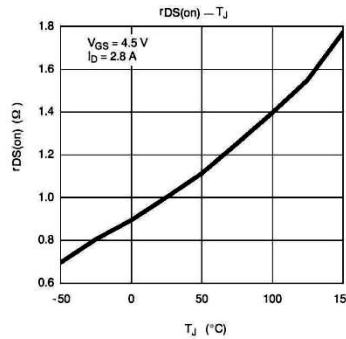
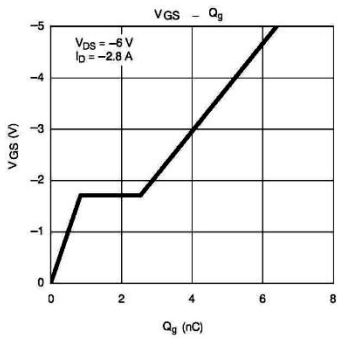
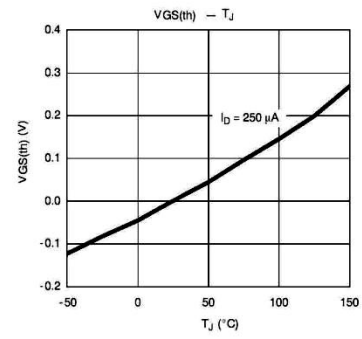
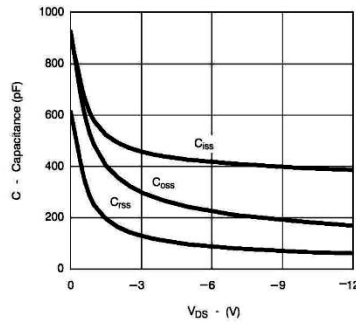
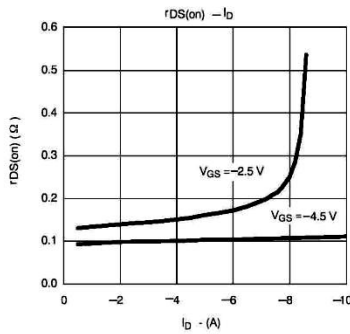
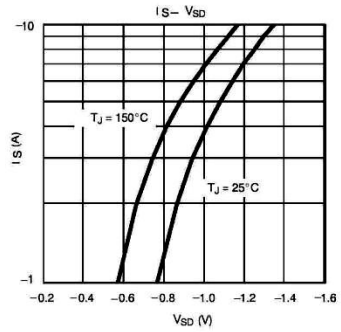
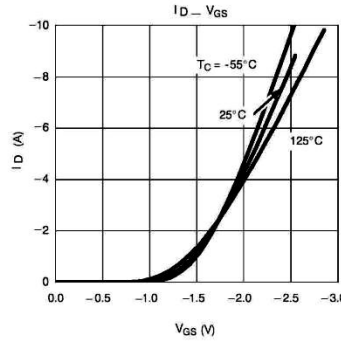
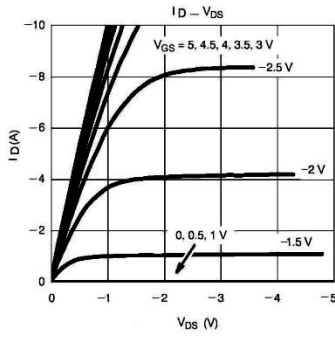
**Absolute Maximum Ratings(Ta=25°C)**

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V <sub>DSS</sub>	-20	V
Gate-Source Voltage	V <sub>GSS</sub>	±8	V
Drain Current – Continuous	I <sub>D</sub>	-2.8	A
Drain Current – Continuous	I <sub>D</sub> (T <sub>A</sub> =70°C)	-1.5	A
Pulsed Drain Current	I <sub>DM</sub>	-10	A
Continuous Source Current (Diode Conduction)	I <sub>S</sub>	-1.6	A
Power Dissipation	P <sub>D</sub>	1.25	W
Power Dissipation	P <sub>D</sub> (T <sub>A</sub> =70°C)	0.8	W
Storage Temperature Range	T <sub>stg</sub>	-55~+150	°C
Operating Junction Temperature Range	T <sub>j</sub>	-55~+150	°C

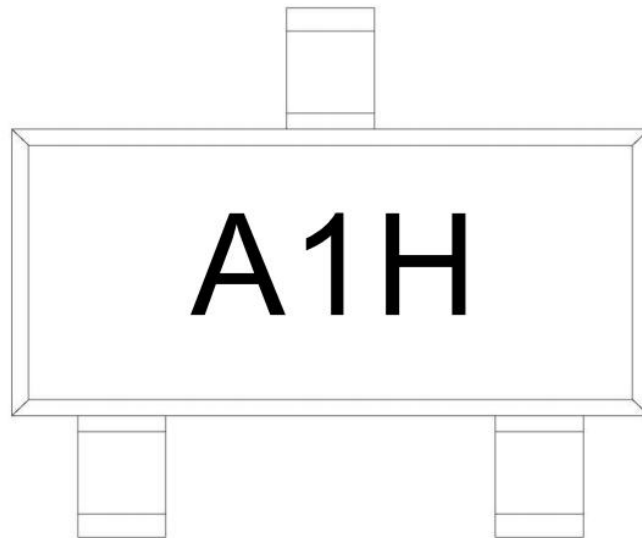
**Electrical Characteristics(Ta=25°C)**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain–Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =-250μA	-20	-23		V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> I <sub>D</sub> =-250μA	-0.45		-0.95	V
Static Drain–Source On–Resistance	R <sub>DS(on)1</sub>	V <sub>GS</sub> =-4.5V I <sub>D</sub> =-2.8A		0.068	0.13	Ω
	R <sub>DS(on)2</sub>	V <sub>GS</sub> =-2.5V I <sub>D</sub> =-2.0A		0.096	0.19	Ω
Zero Gate Voltage Drain Current	I <sub>DSS(1)</sub>	V <sub>DS</sub> =-20V V <sub>GS</sub> =0V			-1	μA
	I <sub>DSS(2)</sub>	V <sub>DS</sub> =-20V V <sub>GS</sub> =0V T <sub>j</sub> =55°C			-10	μA
Gate–Body Leakage	I <sub>GSS</sub>	V <sub>GS</sub> =±8V V <sub>DS</sub> =0V			±0.1	μA
Drain–Source Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-1.6A V <sub>GS</sub> =0V		-0.8	-1.2	V
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =-5V I <sub>D</sub> =-2.8A		6.5		S
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-6V, V <sub>GS</sub> =0V f=1MHz		620		pF
Output Capacitance	C <sub>oss</sub>			390		
Reverse Transfer Capacitance	C <sub>rss</sub>			230		
Turn–On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =-6V R <sub>L</sub> =6Ω I <sub>D</sub> ≈-1A R <sub>G</sub> =6Ω V <sub>GEN</sub> =-4.5V		13	25	ns
Turn–On Rise Time	t <sub>r</sub>			36	60	
Turn–Off Delay Time	t <sub>d(off)</sub>			42	70	
Turn–Off Fall Time	t <sub>f</sub>			34	60	

Electrical Characteristic Curve



**Marking Instructions**



Note:

A1: Product Type Code

H: Company Code.

**Packaging SPEC**

REEL INFORMATION

Package Type	Units					Dimension (unit: mm <sup>3</sup> )		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
SOT-23	3,000	10	30,000	6	180,000	7" x8	180×120×180	390×385×205

**Package Outline Dimensions**

SOT-23

单位: mm

